# Jiamang Che

List of Publications by Year
in descending order



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|---|---|---|---|
| 11 papers | 96 citations | 1478505 6 h-index | 1372567 10 g-index |
| 11 all docs | 11 docs citations | 11 times ranked | 100 citing authors |

| # | Article | IF | Citations |
|---|---|---|---|
| 1 | On the p-AlGaN/n-AlGaN/p-AlGaN Current Spreading Layer for AlGaN-based Deep Ultraviolet Light-Emitting Diodes. Nanoscale Research Letters, 2018, 13, 355. | 5.7 | 22 |
| 2 | Doping-induced energy barriers to improve the current spreading effect for AlGaN-based ultraviolet-B light-emitting diodes. IEEE Electron Device Letters, 2020, , 1-1. | 3.9 | 15 |
| 3 | On the Impact of Electron Leakage on the Efficiency Droop for AlGaN Based Deep Ultraviolet Light Emitting Diodes. IEEE Photonics Journal, 2020, 12, 1-7. | 2.0 | 12 |
| 4 | Modulating the Layer Resistivity by Band-Engineering to Improve the Current Spreading for DUV LEDs. IEEE Photonics Technology Letters, 2019, 31, 1201-1204. | 2.5 | 11 |
| 5 | Interplay between various active regions and the interband transition for AlGaN-based deep-ultraviolet light-emitting diodes to enable a reduced TM-polarized emission. Journal of Applied Physics, 2019, 126, 245702. | 2.5 | 9 |
| 6 | Polarization Self-Screened Multiple Quantum Wells for Deep Ultraviolet Light-Emitting Diodes to Enhance the Optical Power. IEEE Photonics Journal, 2021, 13, 1-5. | 2.0 | 8 |
| 7 | Influence of an Insulator Layer on the Charge Transport in a Metal/Insulator/nâ€AlGaN Structure. Physica Status Solidi (A) Applications and Materials Science, 2019, 216, 1800810. | 1.8 | 5 |
| 8 | On the Carrier Transport for InGaN/GaN Core-Shell Nanorod Green Light-Emitting Diodes. IEEE Nanotechnology Magazine, 2019, 18, 176-182. | 2.0 | 5 |
| 9 | On the impact of a metalâ€“insulatorâ€“semiconductor structured n-electrode for AlGaN-based DUV LEDs. Applied Optics, 2021, 60, 11222. | 1.8 | 4 |
| 10 | On the polarization self-screening effect in multiple quantum wells for nitride-based near ultraviolet light-emitting diodes. Chinese Optics Letters, 2019, 17, 122301. | 2.9 | 3 |
| 11 | Advantage of SiO<sub>2</sub> Intermediate Layer on the Electron Injection for Ti/n-Al<sub>0.60</sub>Ga<sub>0.40</sub>N Structure. IEEE Transactions on Electron Devices, 2020, 67, 3548-3552. | 3.0 | 2 |